Complementary Power Transistors For Isolated Package Applications

Designed for general-purpose amplifier and switching applications, where the mounting surface of the device is required to be electrically isolated from the heatsink or chassis.

Features

- Electrically Similar to the Popular MJE15030 and MJE15031
- No Isolating Washers Required, Reduced System Cost
- High Current Gain-Bandwidth Product
- UL Recognized, File #E69369, to 3500 V_{RMS} Isolation
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	150	Vdc
Collector-Base Voltage	V _{CB}	150	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
$\begin{array}{l} RMS \mbox{ Isolation Voltage (Note 1)} \\ (t=0.3 \mbox{ sec, R.H.} \leq 30\%, T_A = 25^{\circ}C) \\ Per \mbox{ Figure 11} \end{array}$	V _{ISOL}	4500	V _{RMS}
Collector Current – Continuous	Ι _C	8	Adc
Collector Current – Peak	I _{CM}	16	Adc
Base Current	Ι _Β	2	Adc
Total Power Dissipation (Note 2) @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	36 0.286	W W/°C
Total Power Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	PD	2.0 0.016	W W/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	3.5	°C/W
Lead Temperature for Soldering Purposes	ΤL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Proper strike and creepage distance must be provided.

 Measurement made with thermocouple contacting the bottom insulated surface (in a location beneath the die), the devices mounted on a heatsink with thermal grease and a mounting torque of ≥ 6 in. lbs.



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COMPLEMENTARY SILICON POWER TRANSISTORS 8 AMPERES 150 VOLTS, 36 WATTS



G	= Pb-Free Package
А	= Assembly Location

		·····,	
=	Year		

WW = Work Week

Υ

ORDERING INFORMATION

Device	Package	Shipping
MJF15030G	TO-220 FULLPACK (Pb-Free)	50 Units/Rail
MJF15031G	TO-220 FULLPACK (Pb-Free)	50 Units/Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	150	-	Vdc
Collector Cutoff Current ($V_{CE} = 150 \text{ Vdc}, I_B = 0$)	I _{CEO}	-	10	μAdc
Collector Cutoff Current ($V_{CB} = 150 \text{ Vdc}, I_E = 0$)	I _{СВО}	-	10	μAdc
Emitter Cutoff Current ($V_{BE} = 5 \text{ Vdc}, I_C = 0$)	I _{EBO}	-	10	μAdc
ON CHARACTERISTICS (Note 3)	·			
DC Current Gain ($I_C = 0.1 \text{ Adc}, V_{CE} = 2 \text{ Vdc}$) ($I_C = 2 \text{ Adc}, V_{CE} = 2 \text{ Vdc}$) ($I_C = 3 \text{ Adc}, V_{CE} = 2 \text{ Vdc}$) ($I_C = 4 \text{ Adc}, V_{CE} = 2 \text{ Vdc}$)	h _{FE}	40 40 40 20	- - -	_
		Т	ур	
DC Current Gain Linearity (V _{CE} from 2 V to 20 V, I _C from 0.1 A to 3 A) (NPN to PNP)	h _{FE}	2 3		
Collector–Emitter Saturation Voltage $(I_C = 1 \text{ Adc}, I_B = 0.1 \text{ Adc})$	V _{CE(sat)}	-	0.5	Vdc
Base–Emitter On Voltage (I _C = 1 Adc, V _{CE} = 2 Vdc)	V _{BE(on)}	-	1	Vdc
DYNAMIC CHARACTERISTICS		•	·	·
Current Gain – Bandwidth Product (Note 4)	f _T	30	-	MHz

ELECTRICAL CHARACTERISTICS (Tc = 25°C unless otherwise noted)

 $(I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f_{\text{test}} = 10 \text{ MHz})$

3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%.

4. $f_T = |h_{fe}| \bullet f_{test}$.







Figure 2. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 2 and 3 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)}$ < 150°C. $T_{J(pk)}$ may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.





Figure 6. Current Gain — Bandwidth Product



DC CURRENT GAIN



Figure 9. Turn–On Times

t, TIME (µs)

Figure 10. Turn-Off Times

TEST CONDITIONS FOR ISOLATION TESTS*

FULLY ISOLATED PACKAGE



Figure 11. Mounting Position

*Measurement made between leads and heatsink with all leads shorted together.

MOUNTING INFORMATION



Figure 12. Typical Mounting Techniques*

Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in \cdot lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4-40 screw, without washers, and applying a torque in excess of 20 in \cdot lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4-40 screws indicate that the screw slot fails between 15 to 20 in \cdot lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, ON Semiconductor does not recommend exceeding 10 in \cdot lbs of mounting torque under any mounting conditions.

** For more information about mounting power semiconductors see Application Note AN1040.

PACKAGE DIMENSIONS

TO-220 FULLPAK CASE 221D-03 **ISSUE K**



NOTES 1. DIMENSIONING AND TOLERANCING PER ANSI

 Y14.5M, 1982.
CONTROLLING DIMENSION: INCH
221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
С	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
Н	0.118	0.135	3.00 3.4	
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
Ν	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

STYLE 2: PIN 1. BASE COLLECTOR 2. 3. EMITTER

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